

#### 100V PNP MEDIUM POWER TRANSISTOR IN SOT23

#### **Features**

- $BV_{CEO} > -100V$
- $BV_{ECO} > -7V$
- I<sub>C</sub> = -2A Continuous Collector Current
- V<sub>CE(SAT)</sub> < -130mV @ -1A
- $R_{CE(SAT)} = 108m\Omega$  Typical
- $P_D = 1.25W$
- High Peak Current
- Complementary Part Number ZXTN25100BFH
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)

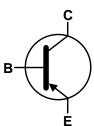
#### **Applications**

- MOSFET and IGBT Gate Driving
- **DC-DC Converters**
- Motor Drive
- Relay, Lamp and Solenoid Drive

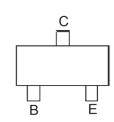








Device Symbol



Top View Pin-Out

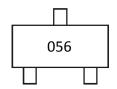
### **Ordering Information** (Note 4)

| Part Number    | Marking | Reel Size (inches) | Tape Width (mm) | Quantity Per Reel |
|----------------|---------|--------------------|-----------------|-------------------|
| ZXTP25100BFHTA | 056     | 7                  | 8               | 3,000             |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



056 = Product Type Marking Code

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#### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                               | Symbol           | Value | Unit |
|--|------------------|-------|------|
| Collector-Base Voltage                       | $V_{CBO}$        | -140  | V    |
| Collector-Emitter Voltage (Forward Blocking) | V <sub>CEO</sub> | -100  | V    |
| Emitter-Collector Voltage (Reverse Blocking) | V <sub>ECO</sub> | -7    | V    |
| Emitter-Base Voltage                         | $V_{EBO}$        | -7    | V    |
| Continuous Collector Current (Note 5)        | Ic               | -2    | Α    |
| Peak Pulse Current                           | I <sub>CM</sub>  | -5    | А    |

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic                          | Symbol               | Value                             | Unit         |      |  |
|---|----------------------|-----------------------------------|--------------|------|--|
|   | (Note 5)             |                                   | 0.73<br>5.84 |      |  |
| Power Dissipation                       | (Note 6)             | Б                                 | 1.05<br>8.4  | W    |  |
| Linear Derating Factor                  | (Note 7)             | P <sub>D</sub>                    | 1.25<br>9.6  | VV   |  |
|   | (Note 8)             |                                   | 1.81<br>14.5 |      |  |
| Thomas Decistors a buestion to Ambient  | (Note 5)<br>(Note 6) |                                   | 171<br>119   | 0000 |  |
| Thermal Resistance, Junction to Ambient | (Note 7)<br>(Note 8) | R <sub>θJA</sub>                  | 100<br>69    | °C/W |  |
| Thermal Resistance, Junction to Lead    | (Note 9)             | $R_{	heta JL}$                    | 74.95        | °C/W |  |
| Operating and Storage Temperature Range | _                    | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150  | °C   |  |

Notes:

- 5. For a device surface mounted on 15mm x 15mm x 1.6mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as note (5), except the device is surface mounted on 25mm x 25mm with 2 oz copper.
- 7. Same as note (5), except the device is surface mounted on 50mm x 50mm with 2 oz copper.
- 8. Same as note (6), except the device is measured at t<5secs.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).

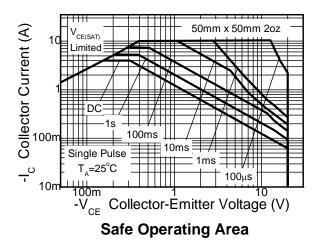
#### ESD Ratings (Note 10)

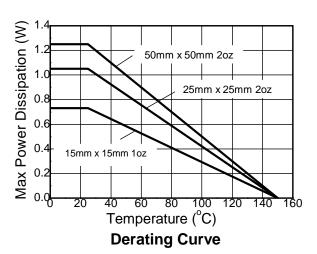
| Characteristic                             | Symbol  | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V    | 3A          |
| Electrostatic Discharge - Machine Model    | ESD MM  | 400   | V    | С           |

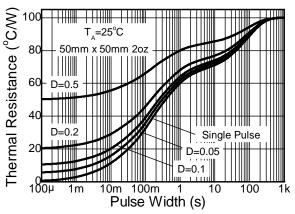
Note: 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

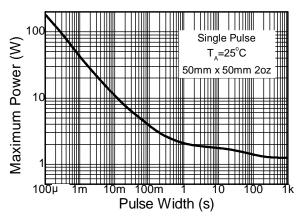


## **Thermal Characteristics and Derating Information**









**Transient Thermal Impedance** 

**Pulse Power Dissipation** 



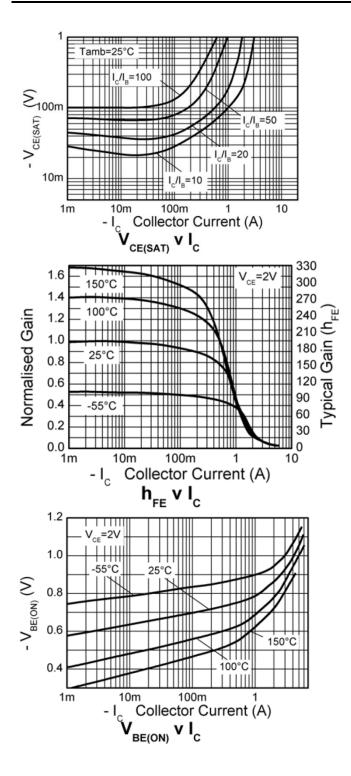
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

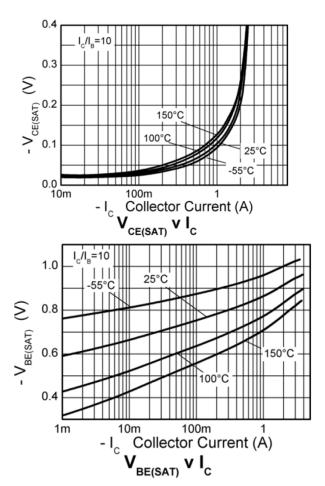
| Characteristic                                  | Symbol               | Min  | Тур  | Max   | Unit | Test Condition  |
|---|----------------------|------|------|-------|------|---|
| Collector-Base Breakdown Voltage                | $BV_CBO$             | -140 | -165 | _     | V    | $I_{C} = -100 \mu A$  |
| Collector-Emitter Breakdown Voltage (Note 11)   | $BV_CEO$             | -100 | -125 | _     | V    | $I_C = -10mA$   |
| Collector-Emitter Breakdown Voltage             | BV <sub>CEX</sub>    | -140 | -165 | _     | V    | $I_E$ = -100μA, $R_{BC}$ < 1k $\Omega$ or -0.25 < $V_{BE}$ < 1V |
| Emitter-Base Breakdown Voltage                  | $BV_EBO$             | -7   | -8.2 | _     | V    | $I_E = -100 \mu A$  |
| Collector-Base Cutoff Current                   | 1                    | _    | < -1 | -50   | nA   | V <sub>CB</sub> = -112V   |
| Collector-base Cutoff Current                   | I <sub>CBO</sub>     | _    | _    | -20   | μΑ   | V <sub>CB</sub> = -112V, T <sub>A</sub> = +100°C                |
| Emitter-Base Cutoff Current                     | I <sub>EBO</sub>     | _    | < -1 | -50   | nA   | V <sub>EB</sub> = -5.6V   |
|   |                      | 100  | 200  | 300   |      | $I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$                     |
| Static Forward Current Transfer Ratio (Note 11) | h <sub>FE</sub>      | 55   | 105  | _     | _    | $I_C = -1A$ , $V_{CE} = -2V$                                    |
|   |                      | 15   | 25   | _     |      | $I_C = -2A$ , $V_{CE} = -2V$                                    |
|   |                      | _    | -60  | -90   |      | $I_C = -0.5A$ , $I_B = -50mA$                                   |
| Collector-Emitter Saturation Voltage (Note 11)  | VCE(SAT)             | _    | -240 | -350  | mV   | $I_C = -0.5A$ , $I_B = -10mA$                                   |
| Collector-Emitter Saturation Voltage (Note 11)  |                      | _    | -100 | -130  | IIIV | $I_C = -1A$ , $I_B = -100mA$                                    |
|   |                      | _    | -215 | -295  |      | $I_C = -2A$ , $I_B = -200mA$                                    |
| Base-Emitter Saturation Voltage (Note 11)       | V <sub>BE(SAT)</sub> | _    | -900 | -1000 | mV   | $I_C = -2A$ , $I_B = -200mA$                                    |
| Base-Emitter Voltage (Note 11)                  | $V_{BE(ON)}$         | _    | -830 | -950  | mV   | $I_C = -2A$ , $V_{CE} = -2V$                                    |
| Output Capacitance                              | Сово                 |      | 15   | 25    | рF   | $V_{CB} = -10V, f = 1MHz$                                       |
| Transition Frequency                            | f⊤                   |      | 200  | _     | MHz  | $V_{CE} = -5V, I_{C} = -100mA,$<br>f = 100MHz                   |
| Turn-on Time                                    | t <sub>(ON)</sub>    |      | 31   | _     | ns   | $V_{CC} = -10V, I_C = -500mA,$                                  |
| Turn-off Time                                   | t <sub>(OFF)</sub>   | _    | 384  | _     | ns   | $I_{B1} = -I_{B2} = -50 \text{mA}$                              |

Note: 11. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)



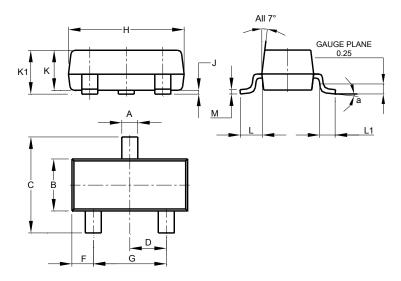




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

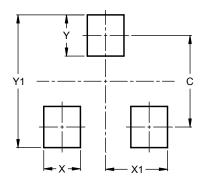


| SOT23                |       |       |       |  |  |
|----------------------|-------|-------|-------|--|--|
| Dim                  | Min   | Max   | Тур   |  |  |
| Α                    | 0.37  | 0.51  | 0.40  |  |  |
| В                    | 1.20  | 1.40  | 1.30  |  |  |
| С                    | 2.30  | 2.50  | 2.40  |  |  |
| D                    | 0.89  | 1.03  | 0.915 |  |  |
| F                    | 0.45  | 0.60  | 0.535 |  |  |
| G                    | 1.78  | 2.05  | 1.83  |  |  |
| Н                    | 2.80  | 3.00  | 2.90  |  |  |
| J                    | 0.013 | 0.10  | 0.05  |  |  |
| K                    | 0.890 | 1.00  | 0.975 |  |  |
| K1                   | 0.903 | 1.10  | 1.025 |  |  |
| L                    | 0.45  | 0.61  | 0.55  |  |  |
| L1                   | 0.25  | 0.55  | 0.40  |  |  |
| М                    | 0.085 | 0.150 | 0.110 |  |  |
| а                    | 0°    | 8°    |       |  |  |
| All Dimensions in mm |       |       |       |  |  |

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 2.0           |
| Х          | 0.8           |
| X1         | 1.35          |
| Υ          | 0.9           |
| Y1         | 2.9           |



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